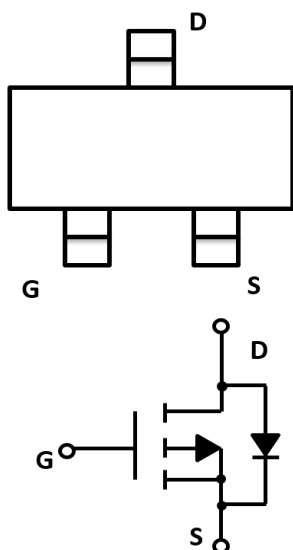


Top View

SOT-23



Product Summary

- V_{DS} -30V
- I_D -4.1A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) <60 mohm
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) <75 mohm

General Description

- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Maximum	Unit
Drain-source Voltage		V_{DS}	-30	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^\circ\text{C}$ @ Steady State	I_D	-4.1	A
	$T_A=70^\circ\text{C}$ @ Steady State		-3.2	
Pulsed Drain Current ^A		I_{DM}	-15	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$		P_D	1.5	W
Thermal Resistance Junction-to-Ambient @ Steady State ^B		$R_{\theta JA}$	82	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERED P/N	Marking	MINIMUM PACKAGE(pcs)	DELIVERY MODE
DMG2307LQ	3407	3000	7" reel

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =-250μA	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V,V _{GS} =0V,T _C =25℃			-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =-250μA	-1.0	-1.5	-2.4	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = -10V, I _D =-4.1A		46	60	mΩ
		V _{GS} = -4.5V, I _D =-3.5A		58	75	
Diode Forward Voltage	V _{SD}	I _S =-4.1A,V _{GS} =0V		-0.8	-1.2	V
Maximum Body-Diode Continuous Current	I _S				-4.1	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-15V,V _{GS} =0V,f=1MHZ		580		pF
Output Capacitance	C _{oss}			98		
Reverse Transfer Capacitance	C _{rss}			74		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =-10V,V _{DS} =-15V,I _D =-4.1A		6.8		nC
Gate Source Charge	Q _{gs}			1.0		
Gate Drain Charge	Q _{gd}			1.4		
Turn-on Delay Time	t _{D(on)}	V _{GS} =-10V,V _{DD} =-15V, R _L =15 Ω ,I _D =-1A, R _{GEN} =2.5Ω		14		ns
Turn-on Rise Time	t _r			61		
Turn-off Delay Time	t _{D(off)}			19		
Turn-off Fall Time	t _f			10		

A. Pulse Test: Pulse Width ≤ 300μs, Duty cycle ≤ 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

■ Typical Performance Characteristics

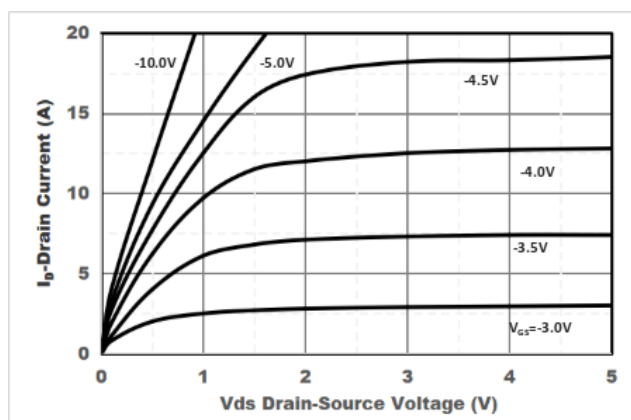


Figure1. Output Characteristics

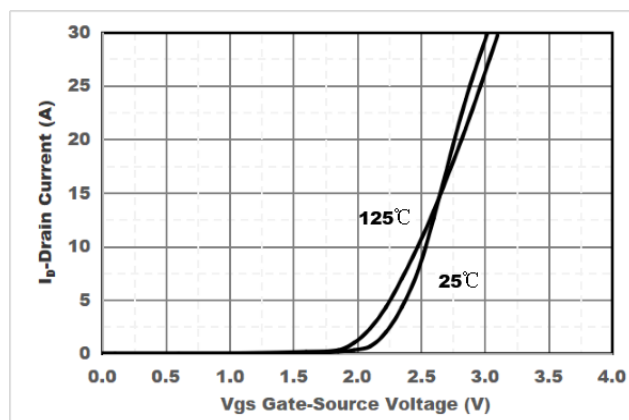


Figure2. Transfer Characteristics

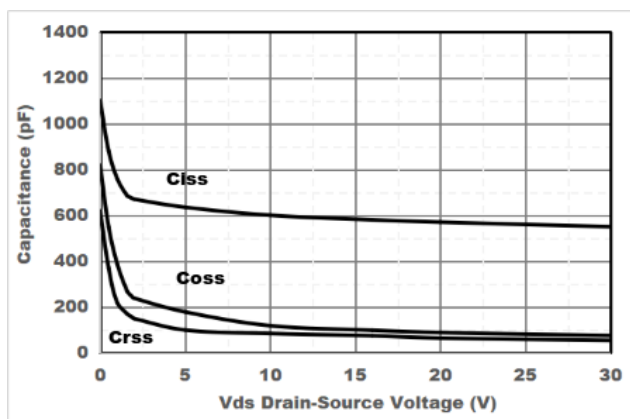


Figure3. Capacitance Characteristics

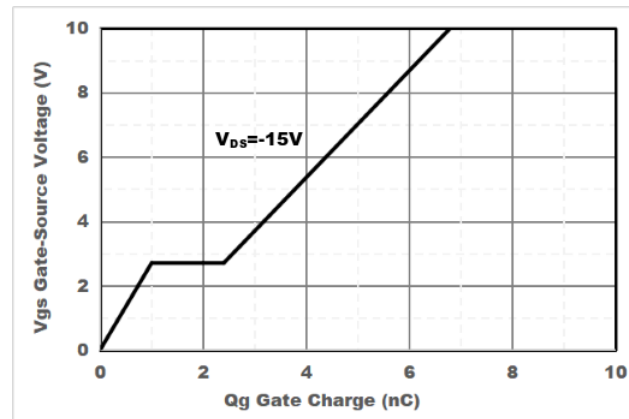


Figure4. Gate Charge

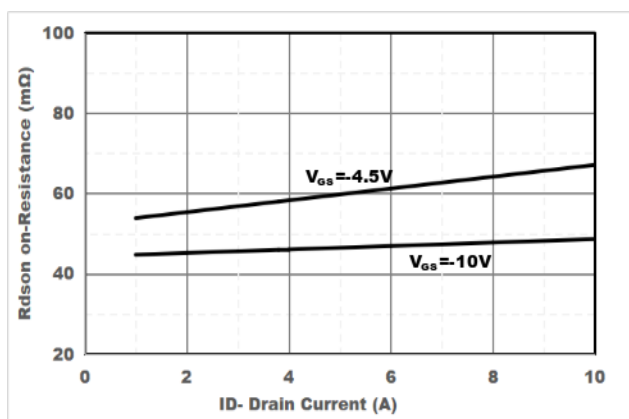


Figure5. Drain-Source on Resistance

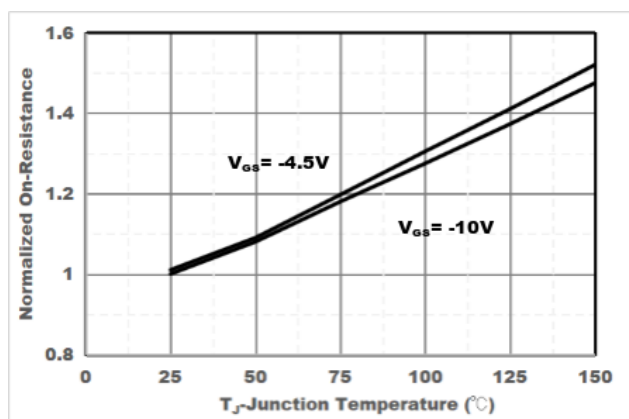


Figure6. Drain-Source on Resistance

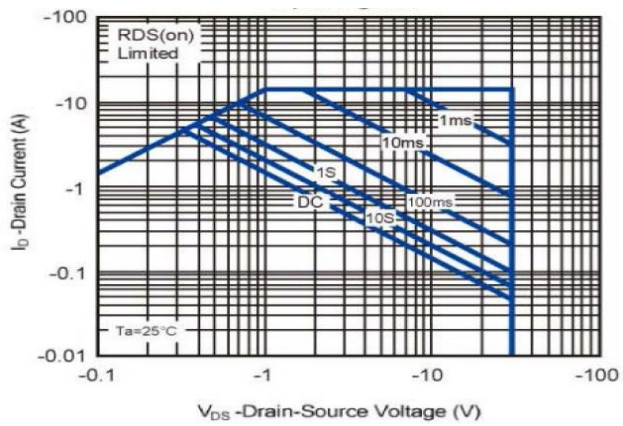


Figure7. Safe Operation Area

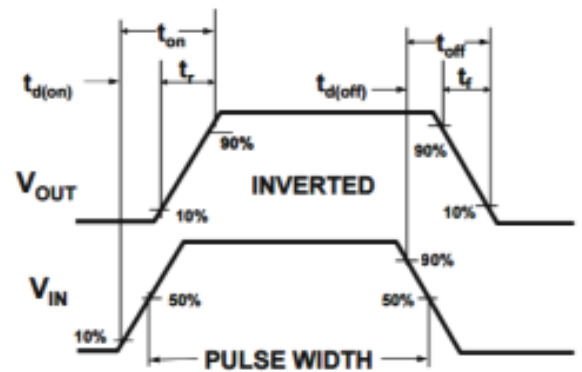
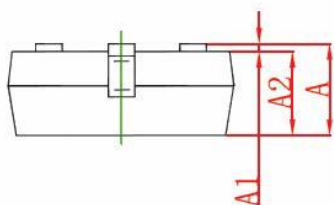
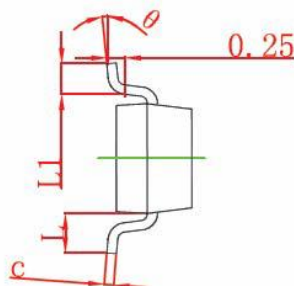
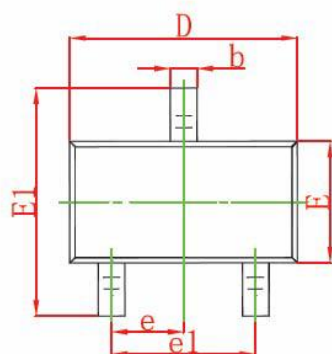


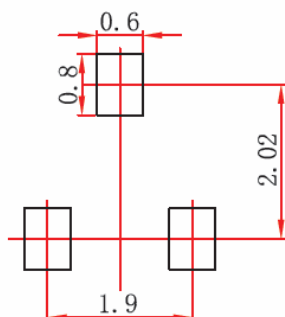
Figure8. Switching wave

■ SOT-23 Package information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

■ SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.